Bipolar Transistor



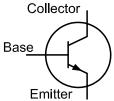




Description:

This TO-3 NPN Transistor is designed for high voltage, high speed, power switching in inductive circuits where fall time is critical. They are particularly suited for line operated switchmode applications.

NPN



Features:

- · Switching Regulators
- Inverters
- · Solenoid and Relay Drivers
- Motor Controls
- · Deflection Circuits

Absolute Maximum Ratings:

Characteristic	Symbol	Rating
Collector - Emitter Voltage	Vcev	700V
Collector - Emitter Voltage	VCEO	400V
Emitter - Base Voltage	VEBO	6V
Continuous Collector Current	Ic	20A
Base Current	lв	10A
Total Device Dissipation (Tc = +25°C) Derate above 25°C	Po	175W 1W/°C
Operating Junction Temperature Range	TJ	-65°C to +200°C
Storage Temperature Range	Tstg	-65°C to +200°C

Electrical Characteristics (TA = 25°C unless otherwise specified)

Parameter	Symbol	Test Conditions	Min.	Max.	Unit
OFF Characteristics					
Collector - Emitter Breakdown Voltage	V(BR)CEO	Ic = 100mA, I _B = 0	400	-	V
Collector Cut-off Current	ICEV	Vce = 700V, VeB(off) = 1.5V	-	0.25	mA
	ICER	Vce = 700V, R _{BE} = 50Ω , Tc = $+100^{\circ}$ C	-	5	mA
Emitter Cut-off Current	ІЕВО	V _{EB} = 6V, I _C = 0	-	1	mA
ON Characteristics (Note 1)					
DC Current Gain	hfe	Vce 5V, Ic = 5A	10	60	-
Collector - Emitter Saturation Voltage	\/o=(==t)	Ic = 10A, I _B = 2A	-	1.8	
	Vce(sat)	Ic = 20A, I _B = 6.7A	-	0.5	V
Base - Emitter Saturation Voltage	V _{BE} (sat)	Ic = 10A, IB = 2A	_	1.8	

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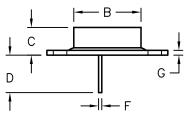


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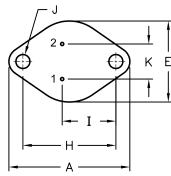


Parameter	Symbol	Test Conditions	Min.	Max.	Unit
Small-Signal Characteristics					
Output Capacitance	Сово	V _{CB} = 10V, I _E = 0, f = 1kHz	125	500	pF
Switching Characteristics					
Delay Time	t _d	V = 050V I = 404 V = 5 5 V I = 04	-	0.1	
Rise Time	t _r	Vcc = 250V, Ic = 10A, VBE(off) = 5V, IB1 = 2A		0.7	
Storage Time	t _S	Vcc = 250V, Ic = 10A, VBE(off) = 5V, IB1 = 2A		4	μs
Fall Time	t _f			0.7	

Note 1: Pulse Test : Pulse Width $\leq 300 \mu s$, Duty Cycle $\leq 2\%$



Pin 1 = Base
Pin 2 = Emitter
Collector (Case)



Dim.	Min.	Max.
А	38.75	39.96
В	19.28	22.23
С	7.96	9.23
D	11.18	12.19
E	25.2	26.67
F	0.92	1.09
G	1.38	1.62
Н	29.9	30.4
I	16.64	17.3
J	3.88	4.36
K	10.67	11.18

Dimensions: Millimetres

Part Number Table

Description	Part Number		
Transistor, Power Switching, High Voltage, Bipolar, TO-3, NPN, 20A, 400V	MJ13333		

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